@PFDesktop\::ODMA/MHODMA/iManage;397072;1 NSP/KTS/dab 07/15/03

(Filed after payment of issue fee)

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applic	cant:	Duy-Phach Vu, Brenda D. Dingle, Jason E. Dingle and Ngwe Cheong
	nuation Applicate olication No.:	tion 09/465,140
Filed:		December 16, 1999
Title:		METHOD OF FORMING AN ACTIVE MATRIX DISPLAY
		Date: 07-15-03
	E	Date: <u>07-/5-03</u> EXPRESS MAIL LABEL NO. <u>EW 3 149 356134</u> S
		INFORMATION DISCLOSURE STATEMENT
P.O. Bo	issioner for Paten ox 1450 dria, VA 22313-	
Sir:		
This Ir	under 37 CFR	Flosure Statement is submitted: 1.129(a), or sion after Final Rejection)
[X]	(Within any one of the stage in an internation	1.97(b), or e following time periods: three months of filing national application (other than a CPA) or date of entry of the national nal application; or before the mailing date of a first office action on the merits in a non-provisional application, including a r Continued Examination).
[]	under 37 CFR	1.97(c) together with either:
	[ ] a States	ment under 37 CFR 1.97(e), as checked below, or
		.00 fee under 37 CFR 1.17(p), or 1.17(b) time period, but before final action or notice of allowance, whichever occurs first)
[]	under 37 CFR	1.97(d) together with:
	[ ] a State	ment under 37 CFR 1.97(e), as checked below, and
		.00 fee under 37 CFR 1.17(p), or or notice of allowance, whichever occurs first, but on or before payment of the issue fee)
[ ]	under 37 CFR Applicant requ	1.97(i): uests that the IDS and cited reference(s) be placed in the application filewrapper.

Staten	nent Un	<u>der 37 (</u>	<u>CFR_1.97(e)</u>		
[ ]	any co	mmuni	information contained in this Information Disclosure Statement was first cited in cation from a foreign patent office in a counterpart foreign application not more nths prior to the filing of this Information Disclosure Statement; or		
[]	comm knowl in the	unication edge of informa	formation contained in this Information Disclosure Statement was cited in a on from a foreign patent office in a counterpart foreign application, and, to the the undersigned, after making reasonable inquiry, no item of information contained ation disclosure statement was known to any individual designated in 37 CFR than three months prior to the filing of this Information Disclosure Statement.		
Staten	nent Un	der 37 (	(Patent Term Adjustment) Applies to original applications (other than design) filed on or after May 29, 2000		
[ ]	comm was no	unication traceives	Information contained in the Information Disclosure Statement was cited in a son from a foreign patent office in a counterpart application and this communication yed by any individual designated in § 1.56(c) more than thirty days prior to the answer of the answer of the property of the answer of the property of the answer		
[ X]	Enclosed herewith is form PTO-1449:				
	[]	Copies	s of the cited references are enclosed.		
	[X]	Applic	s of cited references are enclosed except those entered in prior application, U.S. cation No. 09/465,140, to which priority under 35 U.S.C. 120 is claimed. The application contains copies of the cited references.		
	[ ]	The list	sted references were cited in the enclosed International Search Report in a expart foreign application.		
	[ ]	The "c	oncise explanation" requirement (non-English references) for reference(s) [ 37 CFR 1.98(a)(3) is satisfied by:		
		[ ]	the explanation provided on the attached sheet.		
		[ ]	the explanation provided in the Specification.		
		[ ]	submission of the enclosed International Search Report.		
		[ ]	submission of the enclosed English-language version of a foreign Search Report and/or foreign Office Action.		
		[ ]	the enclosed English language abstract.		

[ ]	Applic	cant requests that the following n	on-published pending applic	cations be considered:
Examiner's Initials				
		U.S. Patent Application No. [	], by [inventor(s)], filed [	], Docket No.: [ ]
		U.S. Patent Application No. [	], by [inventor(s)], filed [	], Docket No.: [ ]
		U.S. Patent Application No. [	], by [inventor(s)], filed [	], Docket No.: [ ]
		Examiner	Date	_
	[ ]	A copy of each above-cited app	olication, including the curre	nt claims, is enclosed.
	[ ]	A copy of each above-cited app those entered in prior application 35 U.S.C. 120 is claimed.	olication, including the curre on, U.S. Application No. [	nt claims, is enclosed, except ], to which priority under
The Ex	kaminer	r is requested to return a copy of re considered with the next office	the above list of pending apple communication.	plications indicating which
It is re	quested	that the information disclosed h	erein be made of record in the	nis application.
Metho	d of pay	ment:		
[ ]		ek for the fee noted above is encl panying Reply. A copy of this S		cluded in the check with the
[ ]	Please	charge Deposit Account 08-038 ed.	0 in the amount of \$[ ]	. A copy of this Statement is
[X]	Please	charge any deficiency in fees an	d credit any overpayment to	Deposit Account 08-0380.
		R	espectfully submitted,	
		Н	IAMILTON, BROOK, SMIT	ΓΗ & REYNOLDS, P.C.
		В	Kevin T. Shaughnessy Registration No.: 51,014 Telephone: (978) 341-0036 Facsimile: (978) 341-0136	,

Concord, MA 01742-9133 Dated: 7/15/03

@PFDesktop\::ODMA/MHODMA/iManage;397082;1 CONTINUATION OF APPLICATION PTO-1449 REPRODUCED ATTORNEY DOCKET NO. 0717.1063-007 No. 09/465,140 INFORMATION DISCLOSURE CITATION IN AN APPLICATION APPLICANT Duy-Phach Vu, et al. July 15, 2003 FILING DATE CONFIRMATION NO. GROUP (Use several sheets if necessary)

		U.S. P	ATENT DOCUMENTS	
EXAM- INER INI- TIAL	REF. NO.	DOCUMENT NUMBER	ISSUE DATE / PUBLICATION DATE	NAME
	AA	4,575,854	03-11-86	Martin
	AB	4,727,047	02-23-88	Bozler, et al.
	AC	4,774,205	09-27-88	Choi, et al.
	AD	4,769,680	09-06-88	Resor, III, et al.
	AE	4,808,983	02-28-89	Benjamin, et al.
	AF	4,838,654	06-13-89	Hamaguchi, et al.
	AG	4,846,931	07-11-89	Gmitter, et al.
	АН	4,855,255	08-08-89	Goodhue
	AI	4,863,877	09-05-89	Fan, et al.
	AJ	4,870,475	09-26-89	Endo, et al.
	AK	4,883,561	11-28-89	Gmitter, et al.
	AA2	4,935,792	06-19-90	Tanaka, et al.
	AB2	4,961,629	10-09-90	Kato
	AC2	4,965,565	10-23-90	Noguchi
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	AJ2	5,184,235	02-02-93	Sukegawa
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	AB3	5,233,211	08-03-93	Hayashi, et al.
	AC3	5,317,433	05-31-94	Miyawaki, et al.

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	AD3	5,347,154	09-13-94	Takahashi, et al.
	AE3	5,362,671	11-08-94	Zavracky, et al.
	AF3	5,377,031	12-27-94	Vu, et al.
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	АН3	4,837,182	06-06-89	Bozler, et al.
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	AA4	3,862,360	01-21-75	Dill, et al.
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	AC4	5,108,843	04-28-92	Ohtaka, e4t al.
	AD4	4,998,152	03-05-91	Batey, et al.

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	DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION YES NO
 AL	1-195421	08 Jul 89	Japan (English Abstract)	I ES NO
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 AN	63-101831	06 May 88	Japan	
 AO	63-55529	10 Mar 88	Japan	
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AR	Akiyama, M., et al., "Growth of GaAs on Si and Its Application to Fets and LEDs.", Nat. Res. Soc. Symp. Proc., 67:53-64 (1986).	
AS	Allen, et al., "Characterization of Isolated Silicon Epitaxy Material", SPIE, Vol. 945 - Advanced Proof Semiconductor Devices II (3/17-3/18, 1988).	
АТ	Conference Record of the 1991 International Display Research Conference, October 15-17, 1991, IEEE.	
AU	Fan, et al., "Lateral Epitaxy by Seeded Solidification for Growth of Crystal Si Films on Insulators", Applys. Lett., 38, 365, 3-1-81.	
AV	McClelland, et al., "A Technique for Producing Epitaxial Films on Reusable Substrates", Appl. Phys. Lett., 37, 560, 9-15-80.	
AW	McDaniel, D.L., et al., "Vertical Cavity Surface-Emitting Semi-Conductor Laser with CW Injection Laser Pumping", IEEE Photon Technol. Lett., March 23, 1990.	
AX	Milnes, A.G., "Semiconductor Heterojunction Topics: Introduction and Overview", Solid State Electronics, Vol. 29, 2:99-121 (1986).	
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AZ	Weber, J.P., et al., "Effects of Layer Thickness Variations on Vertical Cavity Surface-Emitting DBR Semiconductor Lasers", <u>IEEE Photon Tech. Ltr.</u> , March 23, 1990.	
AR2	Yablonovitch, et al., "Extreme Selectivity in the Lift-Off of Epitaxial GaAs Films", Appl. Phys. Lett., 51, 2222 12-28-87.	
AS2	Sumiyoshi, et al., Device Layer Transferred Poly Si TFT Array for High Resolution Liquid Crystal Projector", IEEE, 7.3.1-7.3.4, 1989.	
AT2	Y. Hayashi, et al., "A New Three Dimensional IC Fabrication Technology, Stacking This Film Dual-CMOS Layers", IEEE IDEM, pps. 657-660, 1991.	
AU2	"3-D Chip on Chip Stacking", Semiconductor International, December 1991.	

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	AV2	Matsumoto, et al., "Liquid Crystal Displays (LCDs)", Electronic Display Devices, (John Wiley and Sons) pps. 29-84.			
	AW2				
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